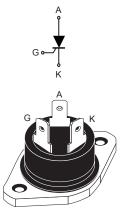
BTW67



Datasheet

50 A,1000 V SCR thyristor in RD91



RD91

F	е	a	tı	J	re)S	

- High current SCR
- High commutation capability
- Low thermal resistance with clip bonding
 - Insulated package RD91 high power:
 - Low thermal resistance with clip bonding
 - Insulated voltage: 2500 V_{RMS}
 - Complies with UL 1557 (File ref : E81734)
- RoHS (2002/95/EC) compliant

Applications

- Solid state relays
- Welding equipment
- High power motor control

Description

Available in 2500 V insulated high power package, the 50 A and 1000 V SCR BTW67 is suitable in applications where power handling and power dissipation are critical, such as solid state relays, welding equipment and high power motor control.

Based on a clip assembly technology, they offer a superior performance in surge current handling capabilities.

Product status link	
BTW67	

Product summary				
I _{T(RMS)}	50 A			
V _{DRM} /V _{RRM}	1000 V			
I _{GT}	80 mA			



1 Characteristics

Symbol	Parameters				Unit
I _{T(RMS)}	RMS on-state current (full sine wave) T _c = 70		T _c = 70 °C	50	Α
IT _(AV)	Average on-state current $T_c = 70 \ ^{\circ}C$ (180° conduction angle)				А
I _{TSM}	Non repetitive surge peak on-state current (full c	ycle, T _j initial = 25 °C)	t _p =8.3 ms	610	Α
l ² t	I ² t value for fusing	t _p = 10 ms		1680	A ² s
dl/dt	Critical rate of rise of on-state current $I_G = 2 \times I_{GT}$, $t_r \le 100 \text{ ns}$	F = 60 Hz	T _j = 125 °C	50	A/µs
I _{GM}	Peak gate current	t _p = 20 μs	T _j = 125 °C	8	Α
P _{G(AV)}	Average gate power dissipation $T_j = 125 \text{ °C}$				W
T _{stg}	Storage junction temperature range			-40 to +150	°C
Tj	Operating junction temperature range			-40 to +125	°C
V _{GRM}	Maximum peak reverse gate voltage			5	V
V _{ins}	Insulation RMS voltage, 1 minute			2500	V

Table 1. Absolute maximum ratings

Table 2. Electrical characteristics (T_j = 25°C, unless otherwise specified)

Symbol	Test conditions T _j			Value	Unit
			Min.	8	~
I _{GT}	V_D = 12 V, R_L = 33 Ω	25 °C	Max	80	mA
V _{GT}			Max	1.3	V
V _{GD}	$V_D = V_{DRM}$, $R_L = 3.3 \text{ k}\Omega$	125 °C	Min.	0.2	V
IH	I _T = 500 mA, gate open		Max.	150	mA
١L	I _G = 1.2 x I _{GT}		Max.	200	mA
dV/dt	V _D = 67 %, V _{DRM} gate open	125 °C	Min.	1000	V/µs
V _{TM}	I _{TM} = 100 A, _{tp} = 380 μs	25 °C	Max.	1.9	V
V _{TO}	threshold on-state voltage	125 °C	Max.	1.0	V
R _D	Dynamic resistance	125 °C	Max.	8.5	mΩ
1 /1		25 °C	Max	10	μA
I _{DRM} /I _{RRM}	$V_D = V_{DRM}, V_R = V_{RRM}$	125 °C	Max.	5	mA

Table 3. Thermal resistance

Symbol	Parameters	Value	Unit
R _{th(j-c)}	Junction to case (D.C)	1.0	°C/W



1.1 Characteristics curves

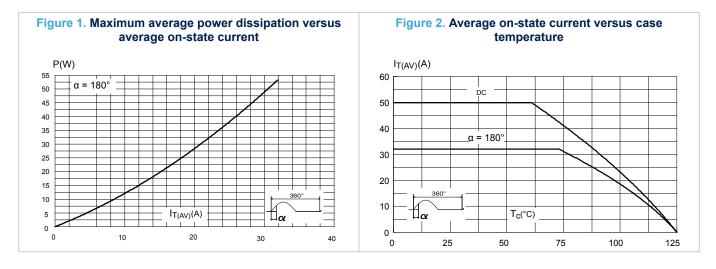
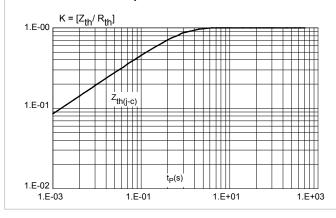
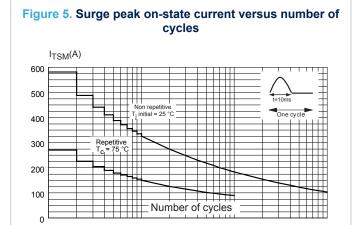


Figure 3. Relative variation of thermal impedance versus pulse duration





100

10

Figure 4. Relative variation of gate trigger current, holding current and latching current versus junction temperature

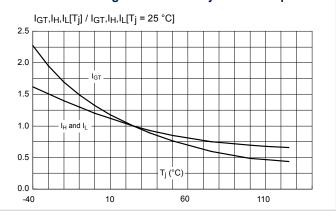
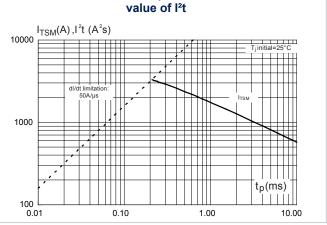


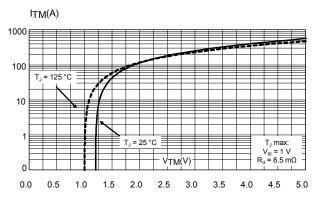
Figure 6. Non repetitive surge peak on-state current for a sinusoidal pulse with width t_p <10ms, and corresponding



1

1000







2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

2.1 RD91 package information

- Epoxy meets UL94, V0
- Cooling method: Conduction
- Recommended torque: 0.9 to 1.2 N·m

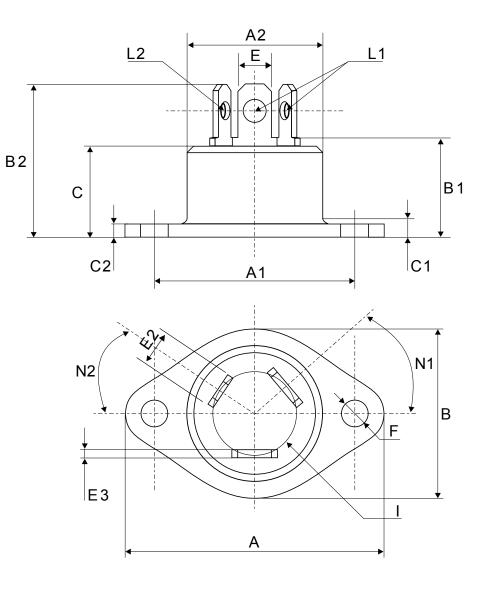


Figure 8. RD91 package outline

Table 4. RD91 mechanical data

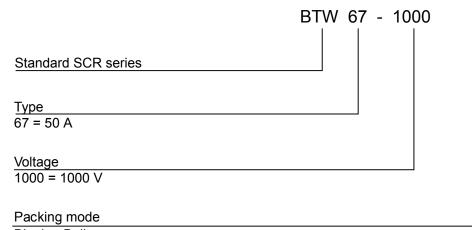
	Dimensions						
Ref.	mm			Inches ⁽¹⁾			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
A			40.00			1.575	
A1	30.10		30.30	1.185		1.193	
A2			22.00			0.867	
В			27.00			1.063	
B1	13.50		16.50	0.531		0.650	
B2			24.00			0.945	
С			14.00			0.552	
C1			3.50			0.138	
C2	1.90		2.10	0.074		0.083	
Е	6.10		6.50	0.240		0.256	
E2	4.80		5.20	0.188		0.205	
E3	0.70		0.90	0.027		0.036	
F	4.00		4.30	0.157		0.170	
I	11.20		11.60	0.440		0.536	
L1	3.10		3.50	0.122		0.138	
L2	1.70		1.90	0.066		0.075	
N1	33°		43°	33°		43°	
N2	28°		38°	28°		38°	

1. Inches given for reference only



3 Ordering information

Figure 9. Ordering information scheme



Blank = Bulk

Table 5. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
BTW67-1000	BTW671000	RD91	20 g	25	Bulk

Revision history

Table 6. Document revision history

Date	Revision	Changes
Apr-2001	4A	Last update.
13-Feb-2006	5	TOP3 Insulated delivery mode changed from bulk to tube. ECOPACK statement added.
26-Jun-2019	6	Removed TOP3 Ins. package information. Minor text changed.
27-Feb-2023	7	Updated package pinout.

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